UP01878

Silicon N-channel MOSFET

For switching

Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

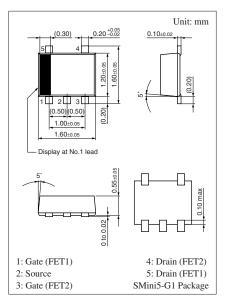
Basic Part Number of Element

• $2SK3539 \times 2$ elements

	Parameter	Symbol	Rating	Unit	
Rating	Drain to source voltage	V _{DSS}	50	V	
of	Gate to source voltage	V _{GSO}	±7	V	
element	Drain current	I _D	100	mA	
	Max drain current	I _{DP}	200	mA	
Overall	Allowable power dissipation *	P_{D}	125	mW	
	Channel temperature	T _{ch}	125	°C	
	Storage temperature	T _{stg}	-55 to +125	°C	

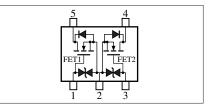
Absolute Maximum Ratings $T_a = 25^{\circ}C$

Note) *: Total power dissipation	Note)	*: 7	Гotal	power	dissipation
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Marking Symbol: AL

Internal Connection

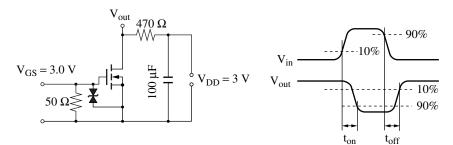


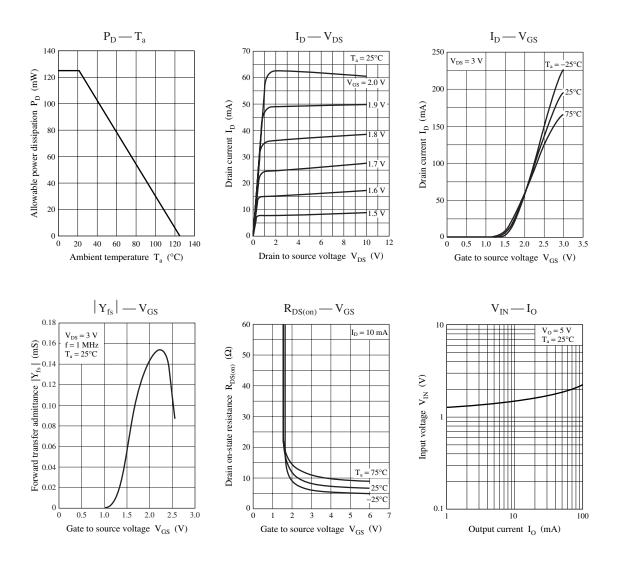
\blacksquare Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain to source voltage	V _{DSS}	$I_{\rm D} = 10 \ \mu A, \ V_{\rm GS} = 0$	50			V
Drain cut-off current	I _{DSS}	$V_{DS} = 50 \text{ V}, V_{GS} = 0$			1.0	μΑ
Gate cut-off current	I _{GSS}	$V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$			±5	μΑ
Gate threshold voltage	V _{th}	$I_{\rm D} = 1 \ \mu A, \ V_{\rm DS} = 3 \ V$	0.9	1.2	1.5	V
Drain on-state resistance	R _{DS(on)}	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		8	15	Ω
		$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$		6	12	
Forward transfer admittance	Y _{fs}	$I_D = 10 \text{ mA}, V_{DS} = 4.0 \text{ V}$	20	60		mS
Input capacitance	C _{iss}	$V_{DS} = 3 V, V_{GS} = 0 V, f = 1 MHz$		12		pF
Output capacitance	C _{oss}			7		pF
Reverse transfer capacitance	C _{rss}			3		pF
Turn-on time *	t _{on}	$V_{DD}{=}3$ V, $V_{GS}{=}0$ V to 3 V, $R_L{=}470\Omega$		200		ns
Turn-off time *	t _{off}	$V_{DD} = 3 V, V_{GS} = 3 V \text{ to } 0 V, R_L = 470 \Omega$		200		ns

Note) *: Refer to t_{on} , t_{off} test circuit (next page)

ton, toff Test circuit





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